



PerF≝T[™]Power Transistor

FEATURES

- Excellent FOM
- Reliability meets AEC-Q101 requirements
- Wettable flank leads for enhanced AOI
- 100% UIS and Rg tested
- 175°C operating junction temperature
- RoHS Compliant
- Halogen-free

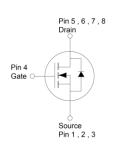
KEY PERFORMANCE PARAMETERS				
PARAMETER		VALUE	UNIT	
V _D	V_{DS}		V	
	V _{GS} = 10V	17		
R _{DS(on)} (max)	V _{GS} = 4.5V	23.8	mΩ	
Q_g	V _{GS} = 4.5V	8.7	nC	



APPLICATIONS

- Solenoid and motor drivers
- DC-DC converters
- Load Switch
- SMPS





Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	100	V	
Gate-Source Voltage		V _G S	±20	V	
Continuous Drain Current	T _C = 25°C		50		
	T _C = 100°C	I _D	36	Α	
	T _A = 25°C		9		
Pulsed Drain Current (Note 1)		I _{DM}	200	Α	
Single Pulse Avalanche Current (Note 2)		las	11.3	Α	
Single Pulse Avalanche Energy (Note 2)		Eas	19	mJ	
Total Power Dissipation	T _C = 25°C	Б	97	W	
	T _C = 125°C	P _D	32		
Operating Junction and Storage Temperature Range		T _J , T _{STG}	- 55 to +175	°C	

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction to Case Thermal Resistance	Rejc	1.54	°C/W	
Junction to Ambient Thermal Resistance (Note 3)	R _{ÐJA}	50	°C/W	

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Notes:

- 1. Pulse Width ≤ 100µs.
- 2. L = 0.3mH, V_{GS} = 10V, R_{G} = 25 Ω , Starting T_{J} = 25 $^{\circ}$ C.
- 3. Device on a PCB FR4 with 1 in² (single layer, 2 oz thickness) copper area for drain connection.



PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$, $I_D = 1mA$	BV _{DSS}	100			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	V _{GS(TH)}	1.4	1.8	2.2	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
	V _{GS} = 0V, V _{DS} = 100V	I _{DSS}			1	μA
Drain-Source Leakage Current	V _G S = 0V, V _D S = 100V T _J = 125°C				100	
Drain-Source On-State Resistance	V _{GS} = 10V, I _D = 25A			12.3	17	mΩ
(Note 4)	V _{GS} = 4.5V, I _D = 25A	R _{DS(on)}		15.8	23.8	
Forward Transconductance (Note 4)	$V_{DS} = 10V, I_D = 6.3A$	G fs		40		S
Dynamic (Note 5)						•
Total Gate Charge	$V_{DS} = 50V, I_{D} = 9A,$ $V_{GS} = 4.5V$	Qg		8.7		nC
Total Gate Charge	V _{DS} = 50V, I _D = 9A,	Qg		17		
Gate-Source Charge		Q _{gs}		3.2		nC
Gate-Drain Charge	V _{GS} = 10V	Q _{gd}		3.4		
Input Capacitance		Ciss		936		
Output Capacitance	$V_{DS} = 60V$, $V_{GS} = 0V$,	Coss		145		pF
Reverse Transfer Capacitance	f = 1.0MHz	Crss		22		
Gate Resistance	f = 1.0MHz	Rg		2		Ω
Switching (Note 6)						
Turn-On Delay Time	$V_{DD} = 50V, R_G = 6\Omega,$ $I_D = 9A, V_{GS} = 10V$	t _{d(on)}		7.3		
Turn-On Rise Time		t _r		19		
Turn-Off Delay Time		t _{d(off)}		21		ns
Turn-Off Fall Time		t _f		28		
Source-Drain Diode						
Forward Voltage (Note 4)	I _S = 25A, V _{GS} = 0V	V _{SD}			1.1	V
Reverse Recovery Time	Is = 9A,	t _{rr}		48		ns
Reverse Recovery Charge	di/dt = 100A/µs	Qrr		51		nC

Notes:

- 4. Pulse test: Pulse Width $\leq 300 \mu s$, duty cycle $\leq 2\%$.
- 5. Defined by design. Not subject to production test.
- 6. Switching time is essentially independent of operating temperature.

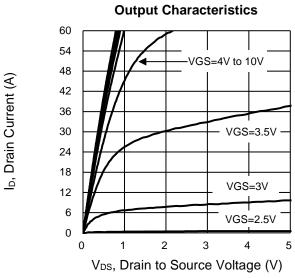
ORDERING INFORMATION

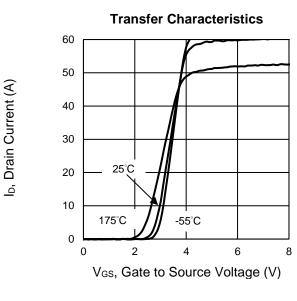
ORDERING CODE	PACKAGE	PACKING
TSM170NH10LCR RLG	PDFN56U	2,500pcs / 13" Reel

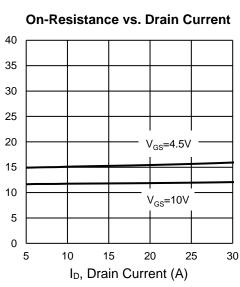


CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$



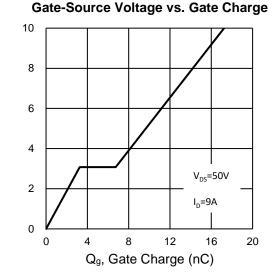


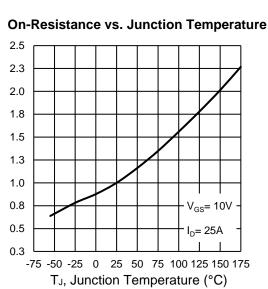


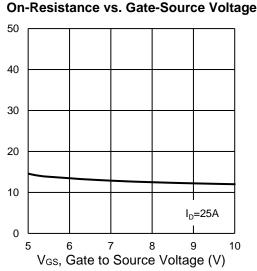
 $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$, Drain-Source On-Resistance $(\mathsf{m}\Omega)$

RDS(on), Drain-Source On-Resistance

(Normalized)





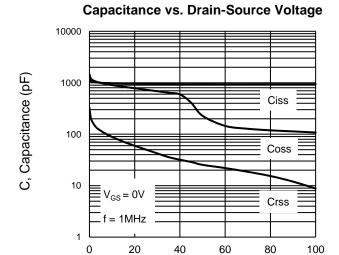


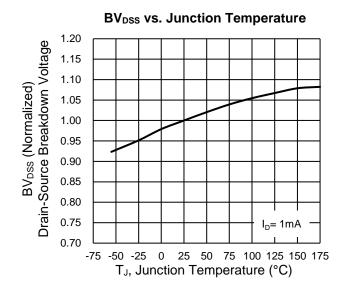
V_{GS}, Gate to Source Voltage (V)



CHARACTERISTICS CURVES

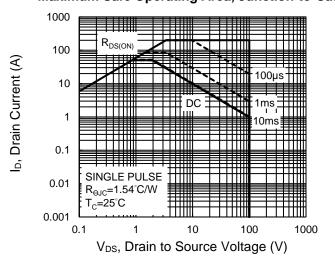
 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$





Maximum Safe Operating Area, Junction-to-Case

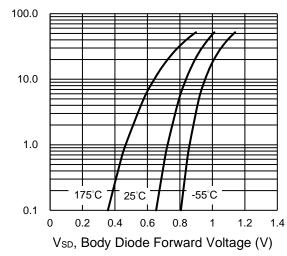
V_{DS}, Drain to Source Voltage (V)



Normalized Effective Transient

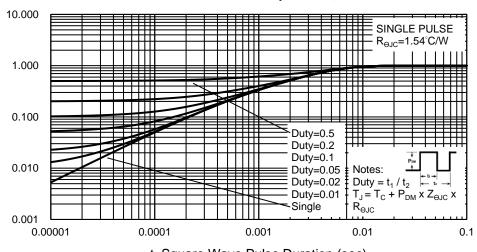
Thermal Impedance, Zeuc

Source-Drain Diode Forward Current vs. Voltage



Normalized Thermal Transient Impedance, Junction-to-Case

ls, Reverse Drain Current (A)



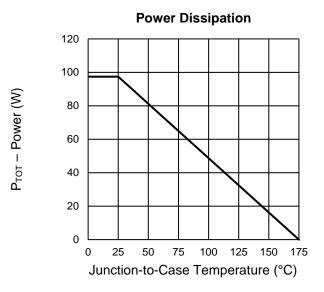
t, Square Wave Pulse Duration (sec)

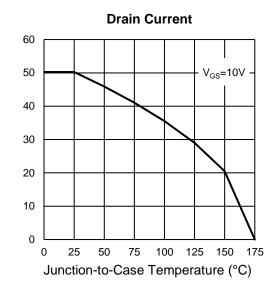


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CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

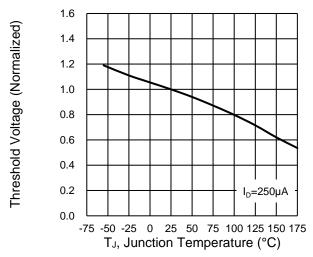




I_D-Drain Current (A)

5

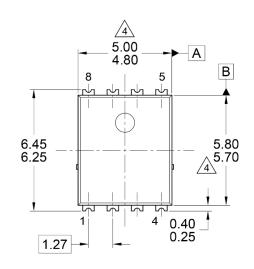
Normalized gate threshold voltage vs Temperature

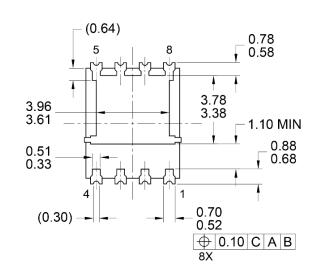


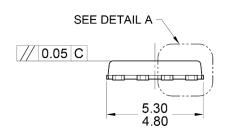


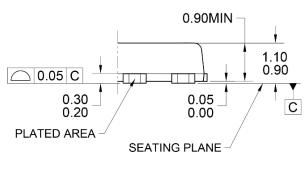
PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

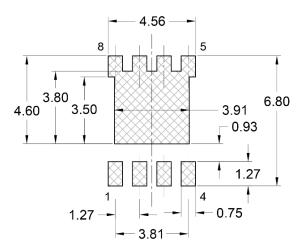
PDFN56U







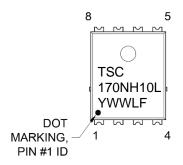




SUGGESTED PAD LAYOUT

(REFERENCE ONLY)

DETAIL A (SCALE 2:1)



NOTES: UNLESS OTHERWISE SPECIFIED

1. ALL DIMENSIONS ARE IN MILLIMETERS.

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- 3. PACKAGE OUTLINE REFERENCE: JEITA ED-7500B, EIAJ SC-111BB.
- MOLDED PLASTIC BODY DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- 5. DWG NO. REF: HQ2SD07-PDFN56U-023 REV B.

MARKING DIAGRAM

170NH10L = Device marking

Y = Year code

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WW = Week code (01~52) L = Lot code (1~9,A~Z)

F = Factory code



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